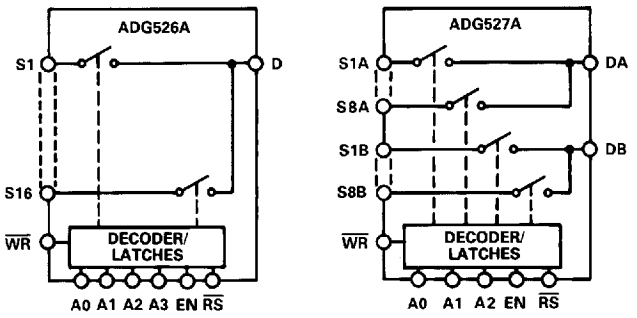
ANALOG DEVICES

CMOS Latched 8/16 Channel Analog Multiplexers

ADG526A/ADG527A

FEATURES
- 44V Supply Maximum Rating
- V_{SS} to V_{DD} Analog Signal Range
- Single/Dual Supply Specifications
- Wide Supply Ranges (10.8V to 16.5V)
- Microprocessor Compatible (100ns $\overline{WR}$ Pulse)
- Extended Plastic Temperature Range (−40°C to +85°C)
- Low Leakage (20pA typ)
- Low Power Dissipation (28mW max)
- Available in DIP, SOIC, PLCC and LCCC Packages
- Superior Alternative to:
  - DG526
  - DG527

FUNCTIONAL BLOCK DIAGRAMS



GENERAL DESCRIPTION

The ADG526A and ADG527A are CMOS monolithic analog multiplexers with 16 channels and dual 8 channels respectively. On-chip latches facilitate microprocessor interfacing. The ADG526A switches one of 16 inputs to a common output depending on the state of four binary addresses and an enable input. The ADG527A switches one of 8 differential inputs to a common differential output depending on the state of three binary addresses and an enable input. Both devices have TTL and 5V CMOS logic compatible digital inputs.

The ADG526A and ADG527A are designed on an enhanced LC^2MOS process which gives an increased signal capability of V_{SS} to V_{DD} and enables operation over a wide range of supply voltages. The devices can comfortably operate anywhere in the 10.8V to 16.5V single or dual supply range. These multiplexers also feature high switching speeds and low R_{ON}.

PRODUCT HIGHLIGHTS

1. Single/Dual Supply Specifications with a Wide Tolerance:
   The devices are specified in the 10.8V to 16.5V range for both single and dual supplies.
2. Easily Interfaced:
   The ADG526A and ADG527A can be easily interfaced with microprocessors. The $\overline{WR}$ signal latches the state of the Address control lines and the Enable line. The $\overline{RS}$ signal clears both the address and enable data in the latches resulting in no output (all switches off). $\overline{RS}$ can be tied to the microprocessor reset pin.
3. Extended Signal Range:
   The enhanced LC^2MOS processing results in a high breakdown and an increased analog signal range of V_{SS} to V_{DD}.
4. Break-Before-Make Switching:
   Switches are guaranteed break-before-make so that input signals are protected against momentary shorting.
5. Low Leakage:
   Leakage currents in the range of 20pA make these multiplexers suitable for high precision circuits.

REV. A

One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.
Tel: 617/329-4700 Fax: 617/326-8703 Twx: 710/394-6577
Telex: 924491 Cable: ANALOG NORWOODMASS

ADG526A/ADG527A—SPECIFICATIONS

Dual Supply (V_{DD} = +10.8V to +16.5V, V_{SS} = −10.8V to −16.5V unless otherwise noted.)

	ADG526A ADG527A K Version		ADG526A ADG527A B Version		ADG526A ADG527A T Version			
Parameter	+25°C	−40°C to +85°C	+25°C	−40°C to +85°C	+25°C	−55°C to +125°C	**Units**	**Comments**
ANALOG SWITCH								
Analog Signal Range	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V min V max	
R_{ON}	280		280		280		Ω typ	−10V≤V_S≤+10V, I_{DS} = 1mA; Test Circuit 1
	450	600	450	600	450	600	Ω max	
	300	400	300	400			Ω max	V_{DD} = 15V(±10%), V_{SS} = −15V(±10%)
					300	400	Ω max	V_{DD} = 15V(±5%), V_{SS} = −15V(±5%)
R_{ON} Drift	0.6		0.6		0.6		%/°C typ	−10V≤V_S≤+10V, I_{DS} = 1mA
R_{ON} Match	5		5		5		% typ	−10V≤V_S≤+10V, I_{DS} = 1mA
I_S (OFF), Off Input Leakage	0.02		0.02		0.02		nA typ	V1 = ±10V, V2 = ∓10V; Test Circuit 2
	1	50	1	50	1	50	nA max	
I_D (OFF), Off Output Leakage	0.04		0.04		0.04		nA typ	V1 = ±10V, V2 = ∓10V; Test Circuit 3
ADG526A	1	200	1	200	1	200	nA max	
ADG527A	1	100	1	100	1	100	nA max	
I_D (ON), On Channel Leakage	0.04		0.04		0.04		nA typ	V1 = ±10V, V2 = ∓10V; Test Circuit 4
ADG526A	1	200	1	200	1	200	nA max	
ADG527A	1	100	1	100	1	100	nA max	
I_{DIFF}, Differential Off Output Leakage (ADG527A only)		25		25		25	nA max	V1 = ±10V, V2 = ∓10V; Test Circuit 5
DIGITAL CONTROL								
V_{INH}, Input High Voltage		2.4		2.4		2.4	V min	
V_{INL}, Input Low Voltage		0.8		0.8		0.8	V max	
I_{INL} or I_{INH}		1		1		1	μA max	V_{IN} = 0 to V_{DD}
C_{IN} Digital Input Capacitance	8		8		8		pF max	
DYNAMIC CHARACTERISTICS[1]								
$t_{TRANSITION}$	200		200		200		ns typ	V1 = ±10V, V2 = ∓10V; Test Circuit 6
	300	400	300	400	300	400	ns max	
t_{OPEN}	50		50		50		ns typ	Test Circuit 7
	25	10	25	10	25	10	ns min	
t_{ON} (EN, $\overline{WR}$)	200		200		200		ns typ	Test Circuits 8 and 9
	300	400	300	400	300	400	ns max	
t_{OFF} (EN, $\overline{RS}$)	200		200		200		ns typ	Test Circuits 8 and 10
	300	400	300	400	300	400	ns max	
t_W Write Pulse Width	100	120	100	120	100	130	ns min	See Figure 1
t_S Address, Enable Setup Time		100		100		100	ns min	See Figure 1
t_H Address, Enable Hold Time		10		10		10	ns min	See Figure 1
t_{RS} Reset Pulse Width		100		100		100	ns min	See Figure 2
OFF Isolation	68		68		68		dB typ	V_{EN} = 0.8V, R_L = 1kΩ, C_L = 15pF,
	50		50		50		dB min	V_S = 7V rms, f = 100kHz
C_S (OFF)	5		5		5		pF typ	V_{EN} = 0.8V
C_D (OFF)								
ADG526A	44		44		44		pF typ	V_{EN} = 0.8V
ADG527A	22		22		22		pF typ	
Q_{INJ}, Charge Injection	4		4		4		pC typ	R_S = 0Ω, V_S = 0V; Test Circuit 11
POWER SUPPLY								
I_{DD}	0.6		0.6		0.6		mA typ	V_{IN} = V_{INL} or V_{INH}
		1.5		1.5		1.5	mA max	
I_{SS}	20		20		20		μA typ	V_{IN} = V_{INL} or V_{INH}
		0.2		0.2		0.2	mA max	
Power Dissipation	10		10		10		mW typ	
		28		28		28	mW max	

NOTE

[1]Sample tested at + 25°C to ensure compliance.

Specifications subject to change without notice.

Single Supply (V_{DD} = +10.8V to +16.5V, V_{SS} = GND = 0V unless otherwise noted.)

Parameter	ADG526A ADG527A K Version +25°C	ADG526A ADG527A K Version −40°C to +85°C	ADG526A ADG527A B Version +25°C	ADG526A ADG527A B Version −40°C to +85°C	ADG526A ADG527A T Version +25°C	ADG526A ADG527A T Version −55°C to +125°C	Units	Comments
ANALOG SWITCH								
Analog Signal Range	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V min V max	
R_{ON}	500 700	 1000	500 700	 1000	500 700	 1000	Ω typ Ω max	0V≤V_S≤+10V, I_{DS} = 0.5mA; Test Circuit 1
R_{ON} Drift	0.6		0.6		0.6		%/°C typ	0V≤V_S≤+10V, I_{DS} = 0.5mA
R_{ON} Match	5		5		5		% typ	0V≤V_S≤+10V, I_{DS} = 0.5mA
I_S (OFF), Off Input Leakage	0.02 1	 50	0.02 1	 50	0.02 1	 50	nA typ nA max	V1 = +10V/0V, V2 = 0V/+10V; Test Circuit 2
I_D (OFF), Off Output Leakage	0.04		0.04		0.04		nA typ	V1 = +10V/0V, V2 = 0V/+10V;
ADG526A	1	200	1	200	1	200	nA max	Test Circuit 3
ADG527A	1	100	1	100	1	100	nA max	
I_D (ON), On Channel Leakage	0.04		0.04		0.04		nA typ	V1 = +10V/0V, V2 = 0V/+10V;
ADG526A	1	200	1	200	1	200	nA max	Test Circuit 4
ADG527A	1	100	1	100	1	100	nA max	
I_{DIFF}, Differential Off Output Leakage (ADG527A only)		25		25		25	nA max	V1 = +10V/0V, V2 = 0V/+10V; Test Circuit 5
DIGITAL CONTROL								
V_{INH}, Input High Voltage		2.4		2.4		2.4	V min	
V_{INL}, Input Low Voltage		0.8		0.8		0.8	V max	
I_{INL} or I_{INH}		1		1		1	μA max	V_{IN} = 0 to V_{DD}
C_{IN} Digital Input Capacitance	8		8		8		pF max	
DYNAMIC CHARACTERISTICS[1]								
$t_{TRANSITION}$	300 450	 600	300 450	 600	300 450	 600	ns typ ns max	V1 = +10V/0V, V2 = 0V/+10V; Test Circuit 6
t_{OPEN}	50 25	 10	50 25	 10	50 25	 10	ns typ ns min	Test Circuit 7
t_{ON} (EN, $\overline{WR}$)	250 450	 600	250 450	 600	250 450	 600	ns typ ns max	Test Circuits 8 and 9
t_{OFF} (EN, $\overline{RS}$)	250 450	 600	250 450	 600	250 450	 600	ns typ ns max	Test Circuits 8 and 10
t_W Write Pulse Width	100	120	100	120	100	130	ns min	See Figure 1
t_S Address, Enable Setup Time		100		100		100	ns min	See Figure 1
t_H Address, Enable Hold Time		10		10		10	ns min	See Figure 1
t_{RS} Reset Pulse Width		100		100		100	ns min	See Figure 2
OFF Isolation	68 50		68 50		68 50		dB typ dB min	V_{EN} = 0.8V, R_L = 1kΩ, C_L = 15pF, V_S = 3.5V rms, f = 100kHz
C_S (OFF)	5		5		5		pF typ	V_{EN} = 0.8V
C_D (OFF)								
ADG526A	44		44		44		pF typ	V_{EN} = 0.8V
ADG527A	22		22		22		pF typ	
Q_{INJ}, Charge Injection	4		4		4		pC typ	R_S = 0Ω, V_S = 0V; Test Circuit 11
POWER SUPPLY								
I_{DD}	0.6	 1.5	0.6	 1.5	0.6	 1.5	mA typ mA max	V_{IN} = V_{INL} or V_{INH}
Power Dissipation	11	 25	11	 25	11	 25	mW typ mW max	

NOTE
[1]Sample tested at +25°C to ensure compliance.
Specifications subject to change without notice.

TIMING DIAGRAMS

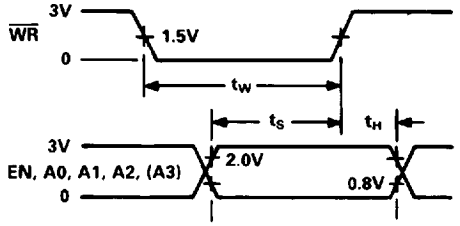


Figure 1.

Figure 1 shows the timing sequence for latching the switch address and enable inputs. The latches are level sensitive; therefore, while $\overline{WR}$ is held low, the latches are transparent and the switches respond to the address and enable inputs. This input data is latched on the rising edge of $\overline{WR}$.

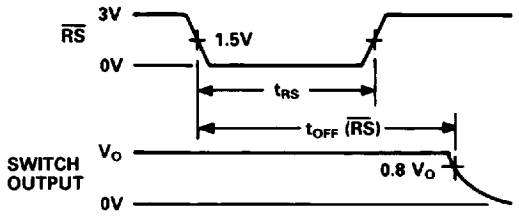


Figure 2.

Figure 2 shows the Reset Pulse Width, t_{RS}, and Reset Turn-off Time, t_{OFF} ($\overline{RS}$).

Note: All digital input signals rise and fall times measured from 10% to 90% of 3V. $t_R = t_F = 20ns$.

ABSOLUTE MAXIMUM RATINGS*

(T_A = +25°C unless otherwise noted)

V_{DD} to V_{SS} 44V
V_{DD} to GND 25V
V_{SS} to GND . . . . . −25V
Analog Inputs[1]
Voltage at S, D . . . . . V_{SS} −2V to V_{DD} +2V or 20mA, Whichever Occurs First
Continuous Current, S or D 20mA
Pulsed Current S or D
1ms Duration, 10% Duty Cycle 40mA
Digital Inputs[1]
Voltage at A, EN, $\overline{WR}$, $\overline{RS}$ . . . . . V_{SS} −4V to V_{DD} +4V or 20mA, Whichever Occurs First
Power Dissipation (Any Package)
Up to +75°C 470mW
Derates above +75°C by . . . . . 6mW/°C

Operating Temperature
Commerical (K Version) . . . . . −40°C to +85°C
Industrial (B Version) . . . . . −40°C to +85°C
Extended (T Version) . . . . . −55°C to +125°C
Storage Temperature Range . . . . . −65°C to +150°C
Lead Temperature (Soldering, 10sec) . . . . . +300°C

NOTE
[1]Overvoltage at A, EN, $\overline{WR}$, $\overline{RS}$, S or D will be clamped by diodes. Current should be limited to the maximum rating above.

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION:
ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are inserted.

ORDERING GUIDE

Model[1]	Temperature Range	Package Option[2]
ADG526AKN	−40°C to +85°C	N-28
ADG526AKR	−40°C to +85°C	R-28
ADG526AKP	−40°C to +85°C	P-28A
ADG526ABQ	−40°C to +85°C	Q-28
ADG526ATQ[3]	−55°C to +125°C	Q-28
ADG526ATE[3]	−55°C to +125°C	E-28A
ADG527AKN	−40°C to +85°C	N-28
ADG527AKR	−40°C to +85°C	R-28
ADG527AKP	−40°C to +85°C	P-28A
ADG527ABQ	−40°C to +85°C	Q-28
ADG527ATQ[3]	−55°C to +125°C	Q-28
ADG527ATE[3]	−55°C to +125°C	E-28A

NOTES
[1]To order MIL-STD-883, Class B processed parts, add /883B to part number. See Analog Devices Military Products Databook (1990) for military data.
[2]E = Leadless Ceramic Chip Carrier; N = Narrow Plastic DIP; P = Plastic Leaded Chip Carrier; Q = Cerdip; R = 0.3" Small Outline IC (SOIC).
[3]Standard Military Drawing (SMD) assigned by DESC. SMD numbers are
5962-89710013X (ADG526ATE/883B)
5962-8971001XX (ADG526ATQ/883B)
5962-89710023X (ADG527ATE/883B)
5962-8971002XX (ADG527ATQ/883B)

TRUTH TABLES

A3	A2	A1	A0	EN	$\overline{WR}$	$\overline{RS}$	ON SWITCH
X	X	X	X	X	↓	1	Retains Previous Switch Condition
X	X	X	X	X	X	0	NONE (Address and Enable Latches Cleared)
X	X	X	X	0	0	1	NONE
0	0	0	0	1	0	1	1
0	0	0	1	1	0	1	2
0	0	1	0	1	0	1	3
0	0	1	1	1	0	1	4
0	1	0	0	1	0	1	5
0	1	0	1	1	0	1	6
0	1	1	0	1	0	1	7
0	1	1	1	1	0	1	8
1	0	0	0	1	0	1	9
1	0	0	1	1	0	1	10
1	0	1	0	1	0	1	11
1	0	1	1	1	0	1	12
1	1	0	0	1	0	1	13
1	1	0	1	1	0	1	14
1	1	1	0	1	0	1	15
1	1	1	1	1	0	1	16

X = Don't Care

ADG526A

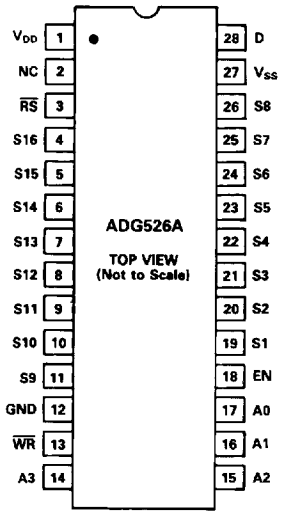
A2	A1	A0	EN	$\overline{WR}$	$\overline{RS}$	ON SWITCH PAIR
X	X	X	X	↓	1	Retains Previous Switch Condition
X	X	X	X	X	0	NONE (Address and Enable Latches Cleared)
X	X	X	0	0	1	NONE
0	0	0	1	0	1	1
0	0	1	1	0	1	2
0	1	0	1	0	1	3
0	1	1	1	0	1	4
1	0	0	1	0	1	5
1	0	1	1	0	1	6
1	1	0	1	0	1	7
1	1	1	1	0	1	8

X = Don't Care

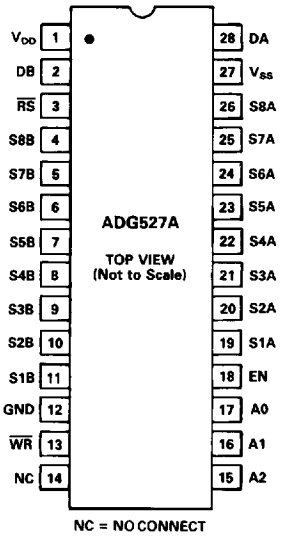
ADG527A

PIN CONFIGURATIONS

DIP, SOIC

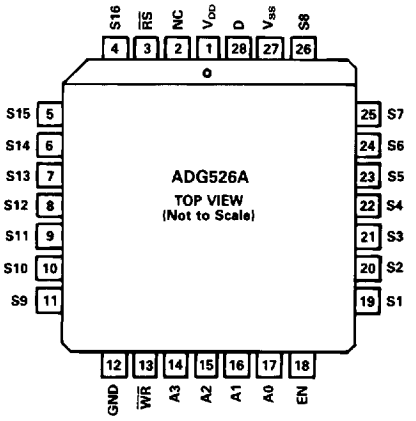


NC = NO CONNECT

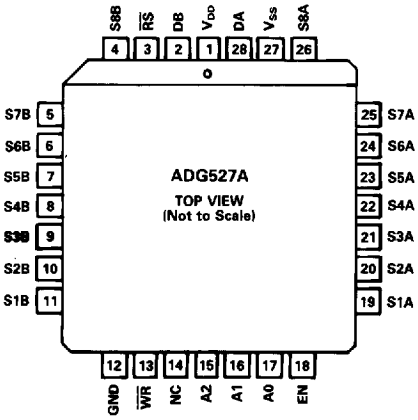


NC = NO CONNECT

LCCC

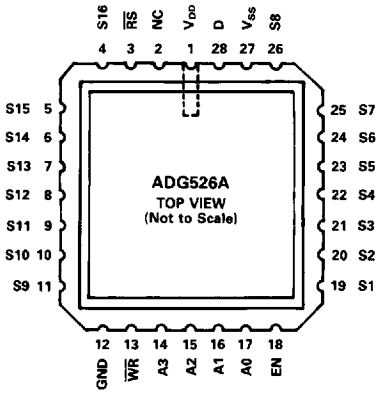


NC = NO CONNECT

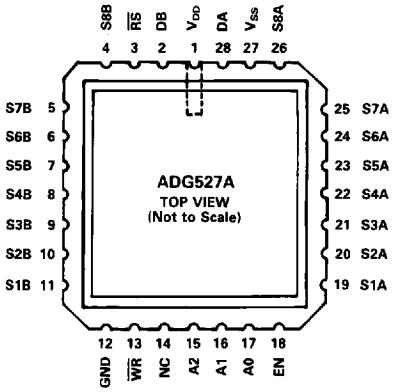


NC = NO CONNECT

PLCC



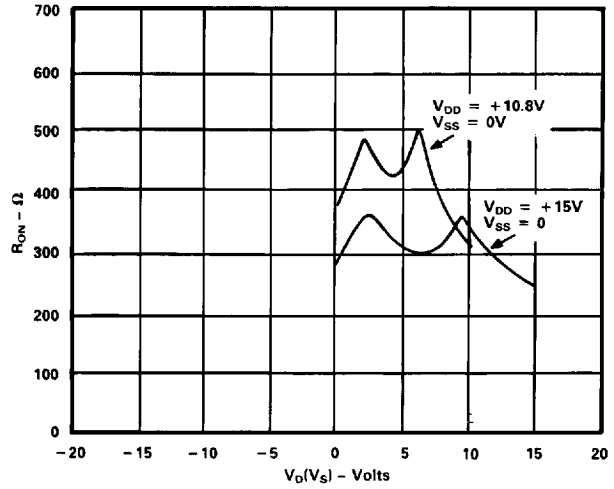
NC = NO CONNECT



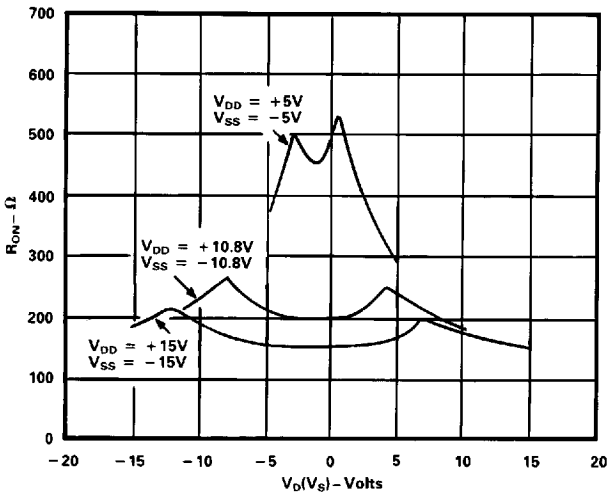
NC = NO CONNECT

Typical Performance Characteristics

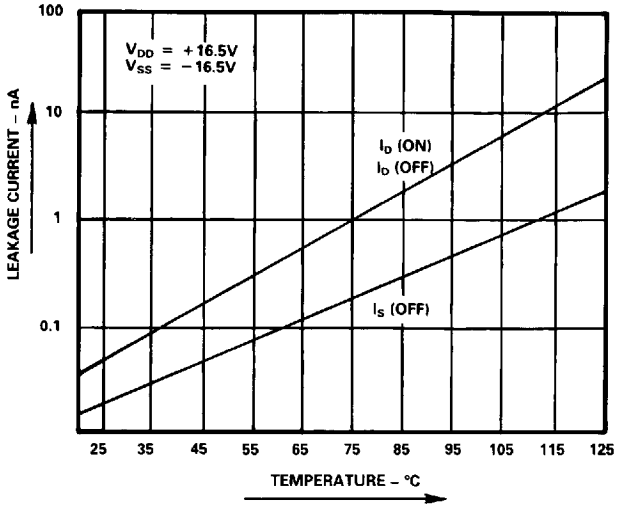
The multiplexers are guaranteed functional with reduced single or dual supplies down to 4.5V.



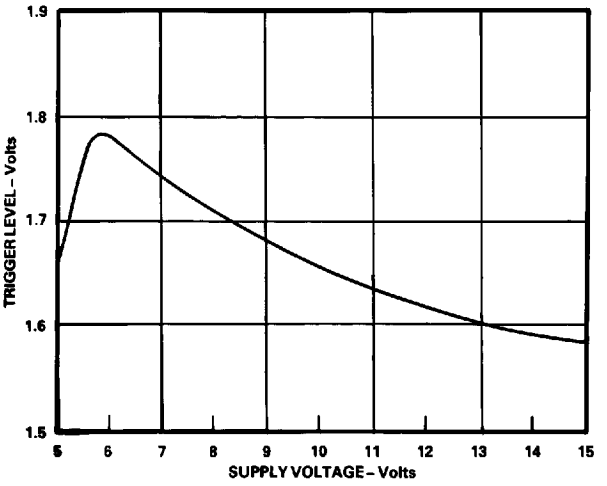
R_{ON} as a Function of $V_D(V_S)$: Dual Supply Voltage, T_A = +25°C



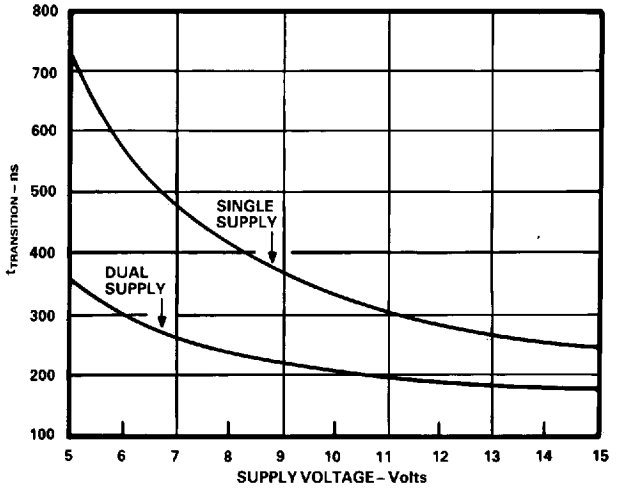
R_{ON} as a Function of $V_D(V_S)$: Single Supply Voltage, T_A = +25°C



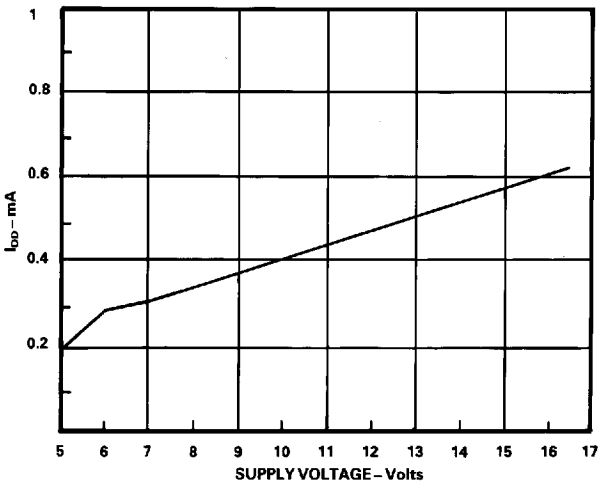
Leakage Current as a Function of Temperature (Note: Leakage Currents Reduce as the Supply Voltages Reduce)



Trigger Levels vs. Power Supply Voltage, Dual or Single Supply, T_A = +25°C

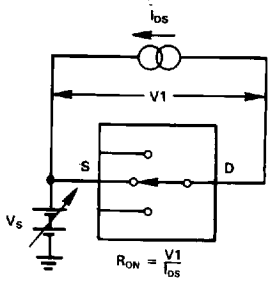


$t_{TRANSITION}$ vs. Supply Voltage: Dual and Single Supplies, T_A = +25°C
(Note: For V_{DD} and $|V_{SS}| < 10V$; V1 = V_{DD}/V_{SS}, V2 = V_{SS}/V_{DD}. See Test Circuit 6)

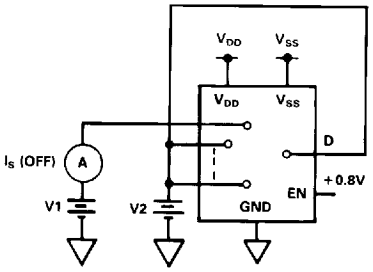


I_{DD} vs. Supply Voltage: Dual or Single Supply, T_A = +25°C

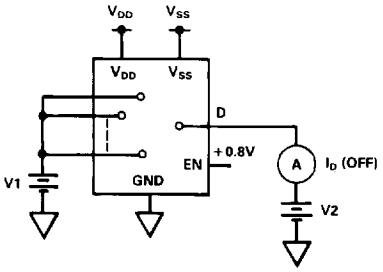
TEST CIRCUIT 1 R_{ON}



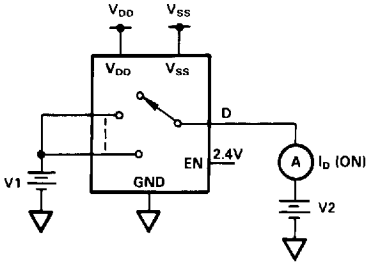
TEST CIRCUIT 2 I_S (OFF)



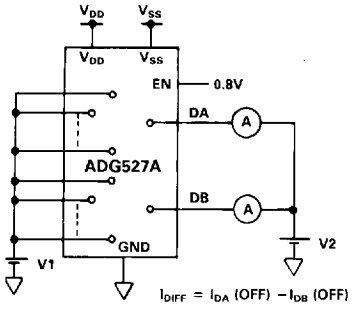
TEST CIRCUIT 3 I_D (OFF)



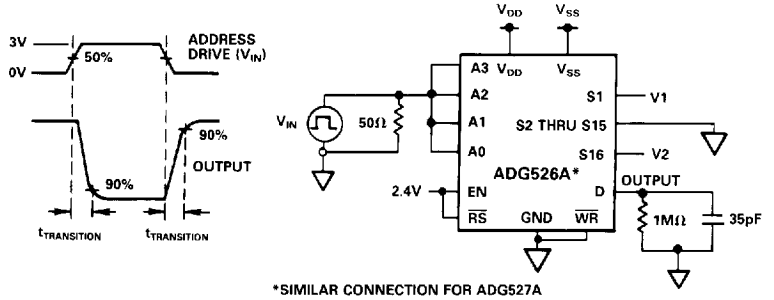
TEST CIRCUIT 4 I_D (ON)



TEST CIRCUIT 5 I_{DIFF}

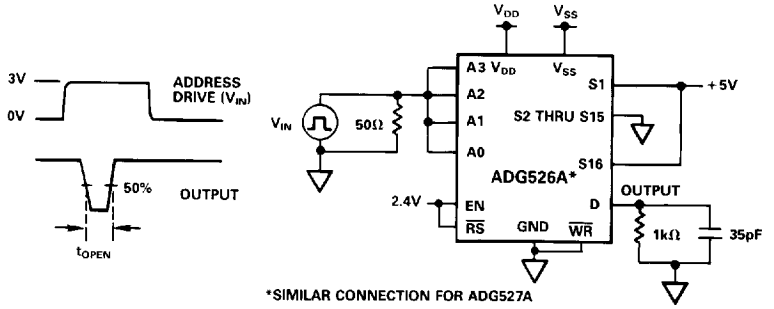


TEST CIRCUIT 6 SWITCHING TIME OF MULTIPLEXER, $t_{TRANSITION}$



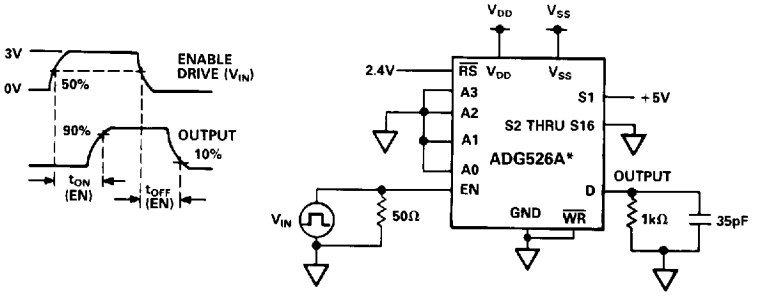
*SIMILAR CONNECTION FOR ADG527A

TEST CIRCUIT 7 BREAK-BEFORE-MAKE DELAY, t_{OPEN}



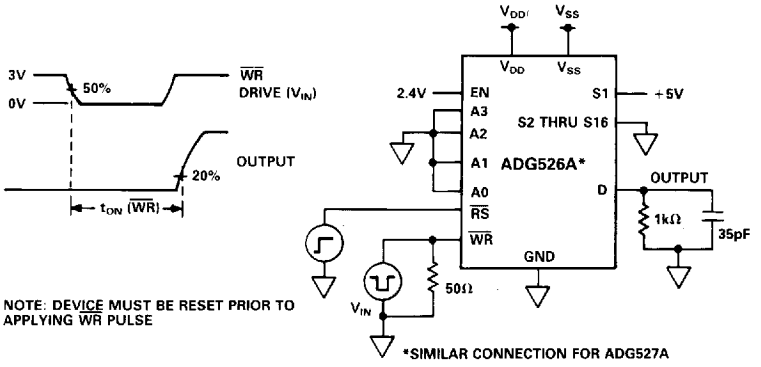
*SIMILAR CONNECTION FOR ADG527A

TEST CIRCUIT 8 ENABLE DELAY, t_{ON} (EN), t_{OFF} (EN)



*SIMILAR CONNECTION FOR ADG527A

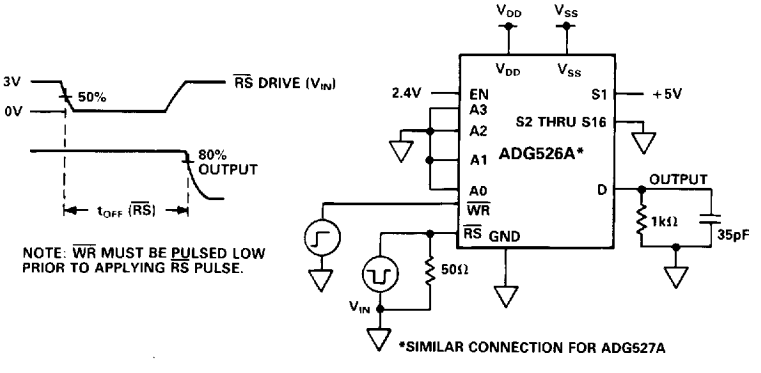
TEST CIRCUIT 9 WRITE TURN-ON TIME, t_{ON} ($\overline{WR}$)



NOTE: DEVICE MUST BE RESET PRIOR TO APPLYING WR PULSE

*SIMILAR CONNECTION FOR ADG527A

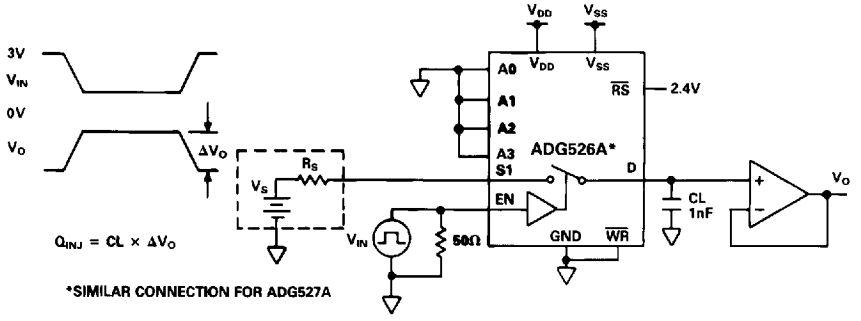
TEST CIRCUIT 10 RESET TURN-OFF TIME, t_{OFF} ($\overline{RS}$)



NOTE: WR MUST BE PULSED LOW PRIOR TO APPLYING RS PULSE.

*SIMILAR CONNECTION FOR ADG527A

TEST CIRCUIT 11 CHARGE INJECTION



TERMINOLOGY

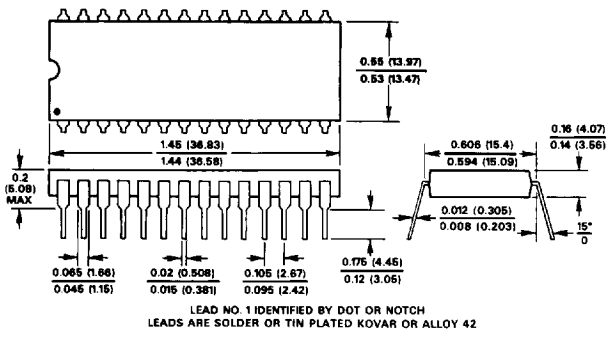
R_{ON}	Ohmic resistance between terminals D and S
R_{ON} Match	Difference between the R_{ON} of any two channels
R_{ON} Drift	Change in R_{ON} versus temperature
I_S (OFF)	Source terminal leakage current when the switch is off
I_D (OFF)	Drain terminal leakage current when the switch is off
I_D (ON)	Leakage current that flows from the closed switch into the body
V_S (V_D)	Analog voltage on terminal S or D
C_S (OFF)	Channel input capacitance for "OFF" condition
C_D (OFF)	Channel output capacitance for "OFF" condition
C_{IN}	Digital input capacitance
t_{ON} (EN)	Delay time between the 50% and 90% points of the digital input and switch "ON" condition
t_{OFF} (EN)	Delay time between the 50% and 10% points of the digital input and switch "OFF" condition
$t_{TRANSITION}$	Delay time between the 50% and 90% points of the digital inputs and switch "ON" condition when switching from one address state to another
t_{OPEN}	"OFF" time measured between 50% points of both switches when switching from one address state to another
V_{INL}	Maximum input voltage for Logic "0"
V_{INH}	Minimum input voltage for Logic "1"
I_{INL} (I_{INH})	Input current of the digital input
V_{DD}	Most positive voltage supply
V_{SS}	Most negative voltage supply
I_{DD}	Positive supply current
I_{SS}	Negative supply current

MECHANICAL INFORMATION

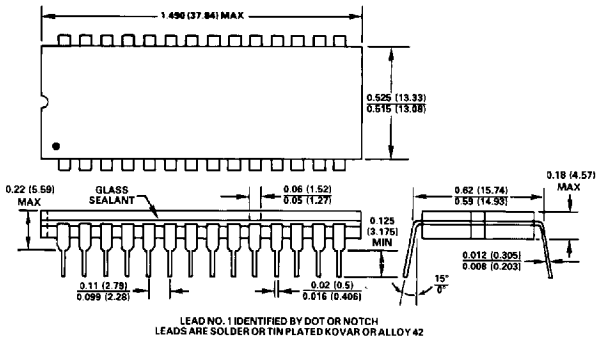
OUTLINE DIMENSIONS

Dimension shown in inches and (mm).

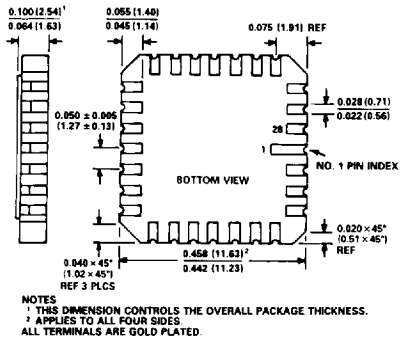
28-Pin Plastic DIP (Suffix N)



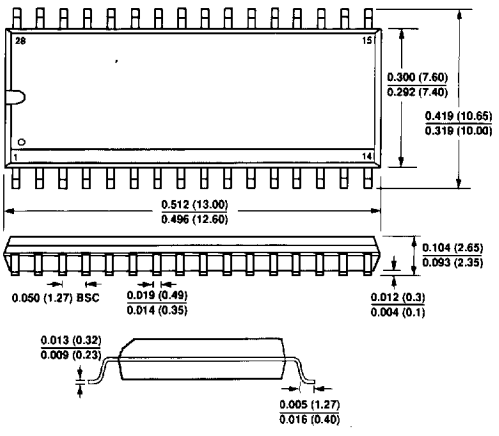
28-Pin Cerdip (Suffix Q)



28-Terminal Leadless Ceramic Chip Carrier (Suffix E)



28-Pin SOIC (R) Package



28-Terminal Plastic Leaded Chip Carrier (Suffix P)